

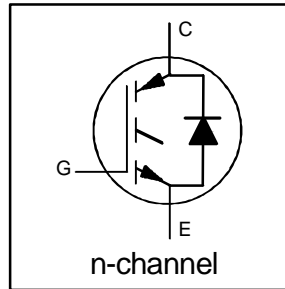
IRGPH50FD2

INSULATED GATE BIPOLAR TRANSISTOR
WITH ULTRAFAST SOFT RECOVERY

Fast CoPack IGBT

DIODE
Features

- Switching-loss rating includes all "tail" losses
- HEXFRED™ soft ultrafast diodes
- Optimized for medium operating frequency (1 to 10kHz) See Fig. 1 for Current vs. Frequency curve



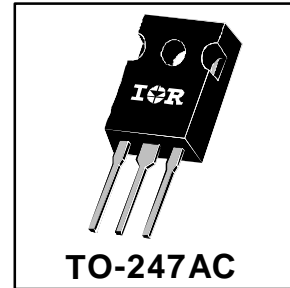
$V_{CES} = 1200V$

$V_{CE(sat)} \leq 2.9V$

@ $V_{GE} = 15V, I_C = 25A$

Description

Co-packaged IGBTs are a natural extension of International Rectifier's well known IGBT line. They provide the convenience of an IGBT and an ultrafast recovery diode in one package, resulting in substantial benefits to a host of high-voltage, high-current, motor control, UPS and power supply applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	45	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	25	
I_{CM}	Pulsed Collector Current ①	90	
I_{LM}	Clamped Inductive Load Current ②	90	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	16	
I_{FM}	Diode Maximum Forward Current	90	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	78	
T_J	Operating Junction and	-55 to +150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	—	0.64	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode	—	—	0.83	
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ③	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu\text{A}$	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.1	—	V/°C	$V_{GE} = 0V, I_C = 1.0\text{mA}$	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.1	2.9	V	$I_C = 25A$ $I_C = 45A$ $I_C = 25A, T_J = 150^\circ\text{C}$	$V_{GE} = 15V$ See Fig. 2, 5
		—	2.5	—			
		—	3.0	—			
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		$V_{CE} = V_{GE}, I_C = 250\mu\text{A}$	
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-14	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu\text{A}$	
g_{fe}	Forward Transconductance ④	7.5	17	—	S	$V_{CE} = 100V, I_C = 25A$	
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 1200V$	
		—	—	6500		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$	
V_{FM}	Diode Forward Voltage Drop	—	2.5	3.0	V	$I_C = 16A$ See Fig. 13	
		—	2.1	2.5		$I_C = 16A, T_J = 150^\circ\text{C}$	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$	

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q_g	Total Gate Charge (turn-on)	—	82	100	nC	$I_C = 25A$ $V_{CC} = 400V$ See Fig. 8	
Q_{ge}	Gate - Emitter Charge (turn-on)	—	16	21			
Q_{gc}	Gate - Collector Charge (turn-on)	—	30	43			
$t_{d(on)}$	Turn-On Delay Time	—	77	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 25A, V_{CC} = 800V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 11, 18	
t_r	Rise Time	—	75	—			
$t_{d(off)}$	Turn-Off Delay Time	—	360	540			
t_f	Fall Time	—	320	470			
E_{on}	Turn-On Switching Loss	—	3.2	—	mJ		
E_{off}	Turn-Off Switching Loss	—	5.8	—			
E_{ts}	Total Switching Loss	—	9.0	13.5			
$t_{d(on)}$	Turn-On Delay Time	—	70	—	ns	$T_J = 150^\circ\text{C}$, See Fig. 9, 10, 11, 18 $I_C = 25A, V_{CC} = 800V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" and diode reverse recovery.	
t_r	Rise Time	—	70	—			
$t_{d(off)}$	Turn-Off Delay Time	—	660	—			
t_f	Fall Time	—	640	—			
E_{ts}	Total Switching Loss	—	16.2	—	mJ		
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package	
C_{ies}	Input Capacitance	—	2400	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0\text{MHz}$ See Fig. 7	
C_{oes}	Output Capacitance	—	140	—			
C_{res}	Reverse Transfer Capacitance	—	28	—			
t_{rr}	Diode Reverse Recovery Time	—	90	135	ns	$T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$	$I_F = 16A$ $V_R = 200V$ $di/dt = 200A/\mu\text{s}$
		—	164	245			
I_{rr}	Diode Peak Reverse Recovery Current	—	5.8	10	A	$T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$	
		—	8.3	15			
Q_{rr}	Diode Reverse Recovery Charge	—	260	675	nC	$T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$	
		—	680	1838			
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	120	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$	
		—	76	—			

Notes:

- ① Repetitive rating; $V_{GE}=20V$, pulse width limited by max. junction temperature. (See fig. 20)
- ② $V_{CC}=80\%(V_{CES}), V_{GE}=20V, L=10\mu\text{H}, R_G = 5.0\Omega$, (See fig. 19)
- ③ Pulse width $\leq 80\mu\text{s}$; duty factor $\leq 0.1\%$.
- ④ Pulse width 5.0 μs , single shot.

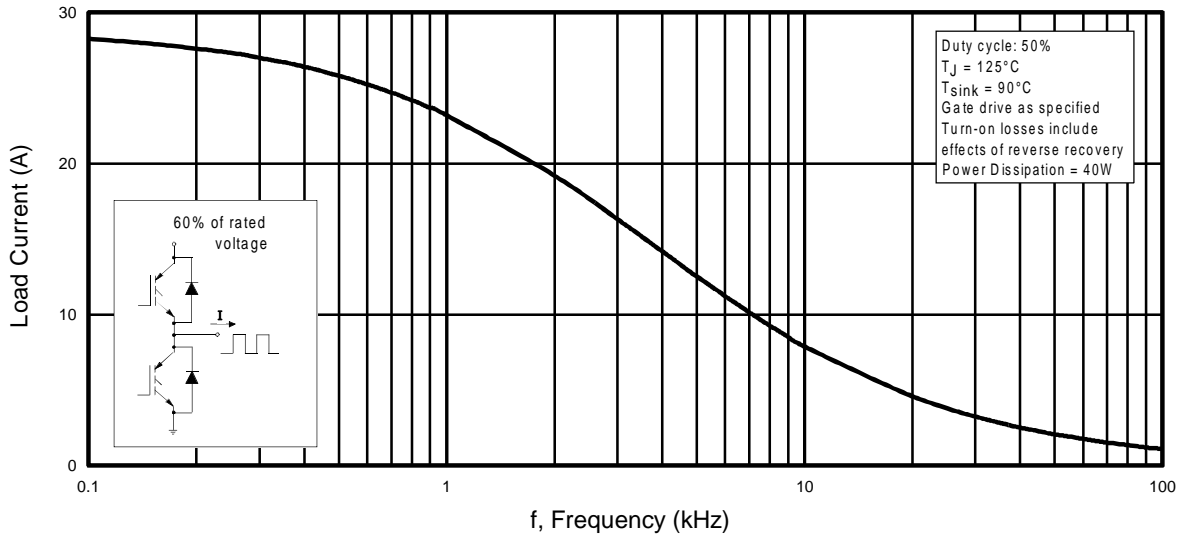


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

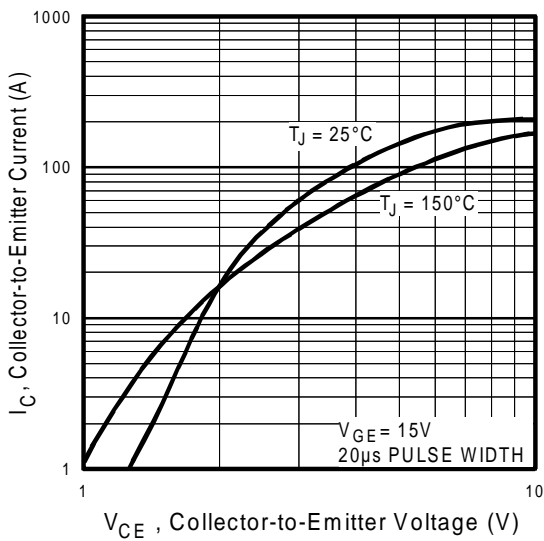


Fig. 2 - Typical Output Characteristics

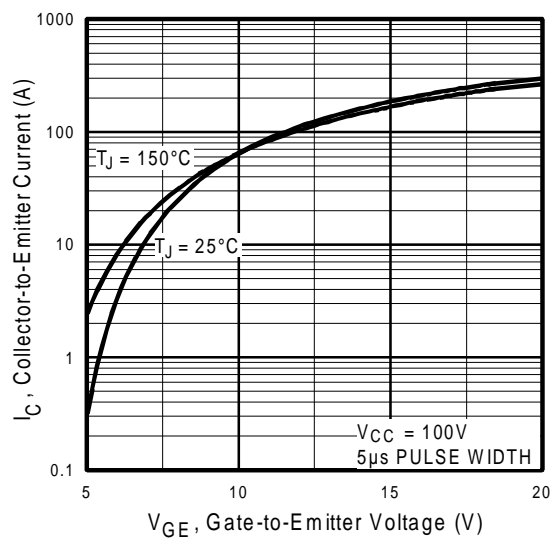


Fig. 3 - Typical Transfer Characteristics

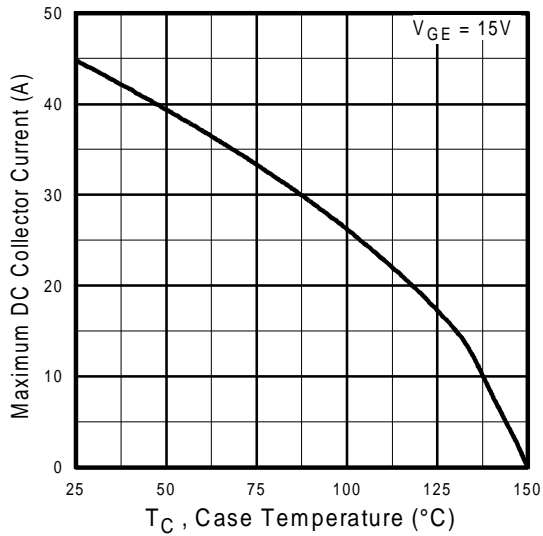


Fig. 4 - Maximum Collector Current vs. Case Temperature

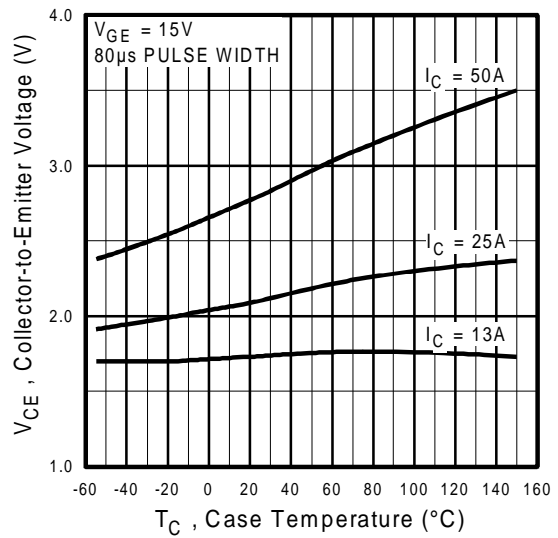


Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

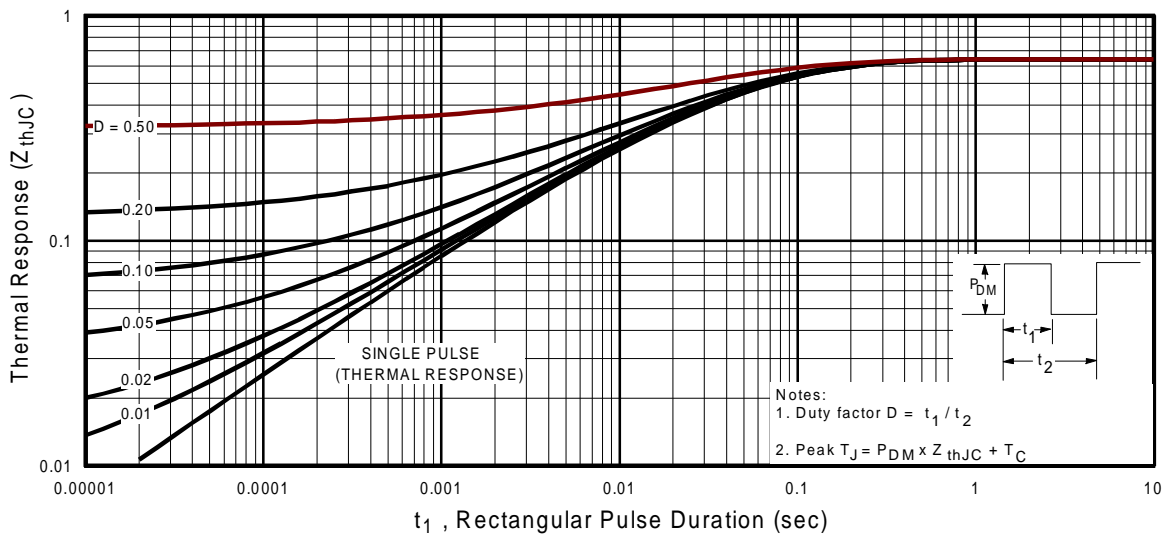


Fig. 6 - Maximum IGBT Effective Transient Thermal Impedance, Junction-to-Case

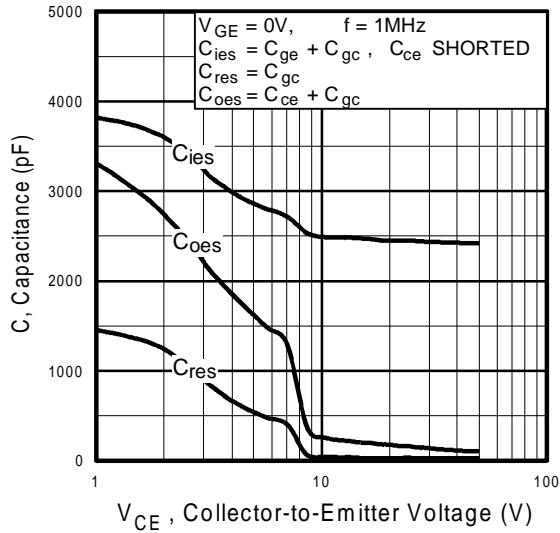


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

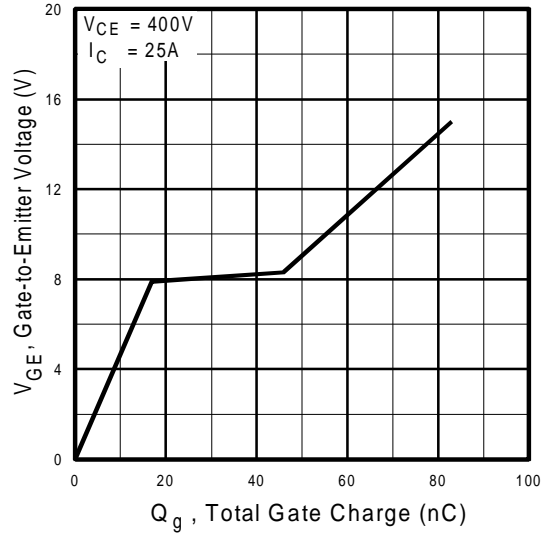


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

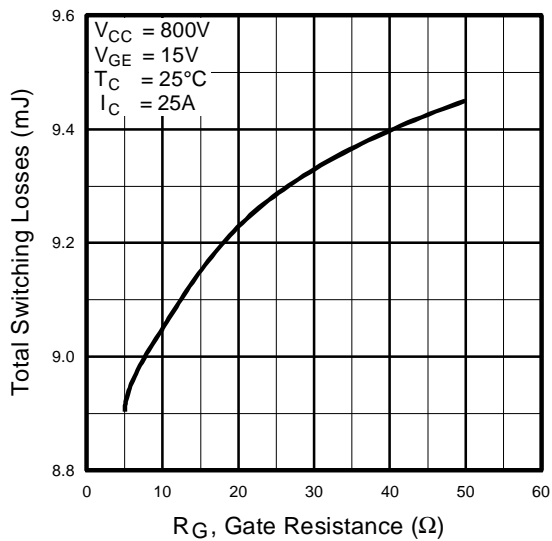


Fig. 9 - Typical Switching Losses vs. Gate Resistance

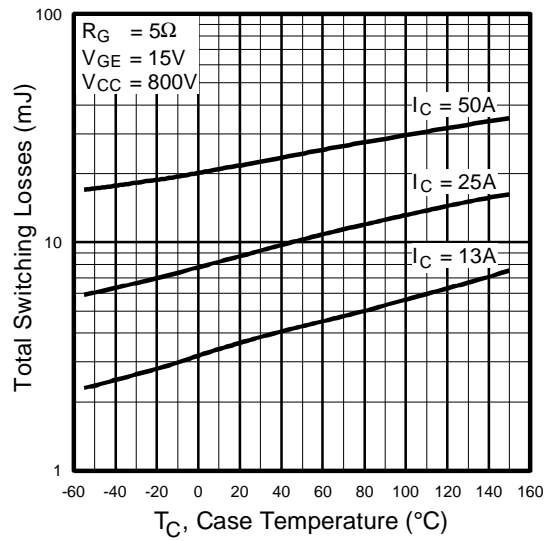


Fig. 10 - Typical Switching Losses vs. Case Temperature

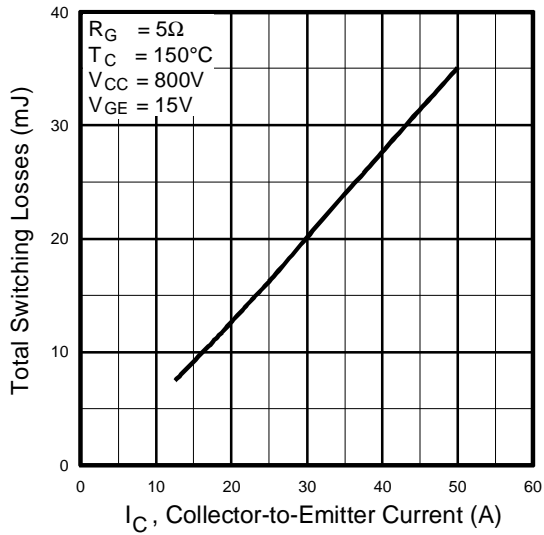


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

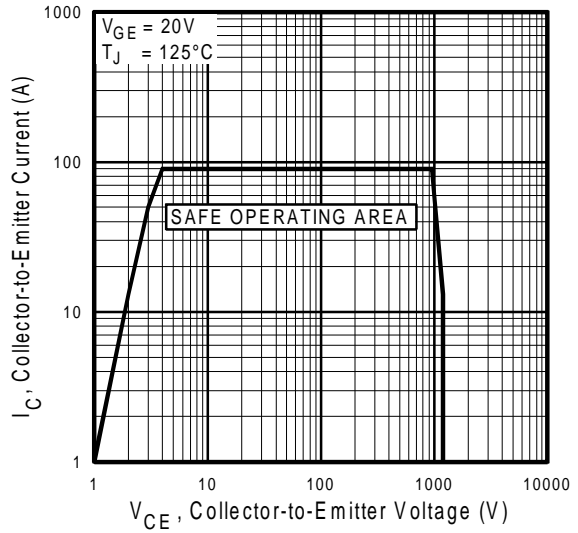


Fig. 12 - Turn-Off SOA

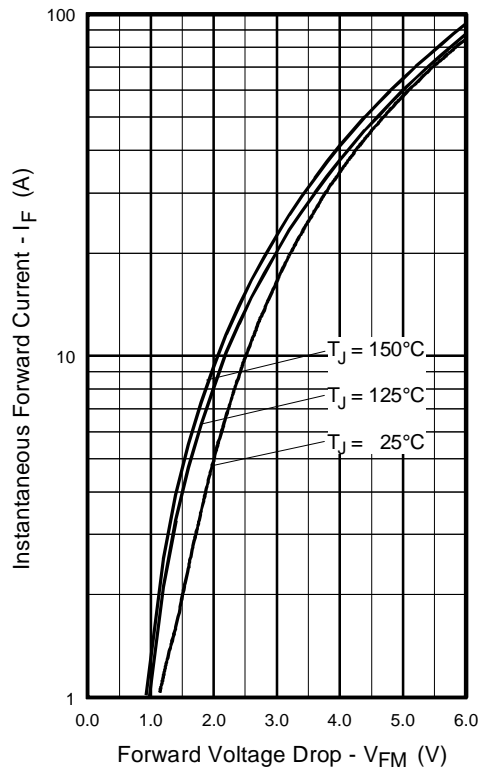


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

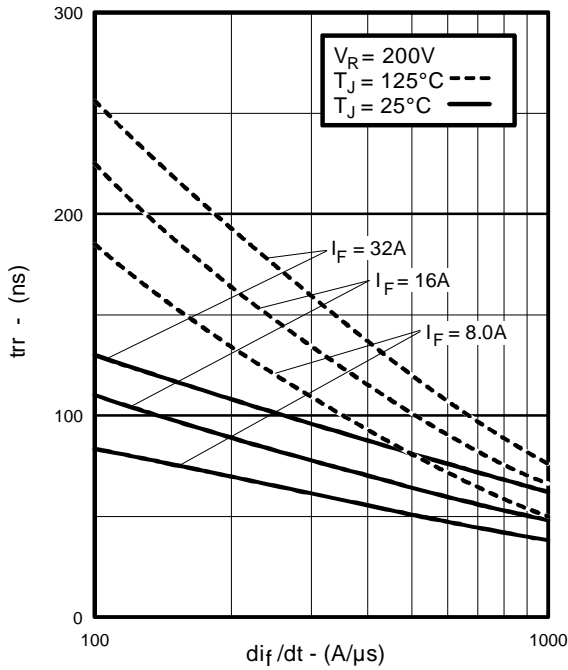


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

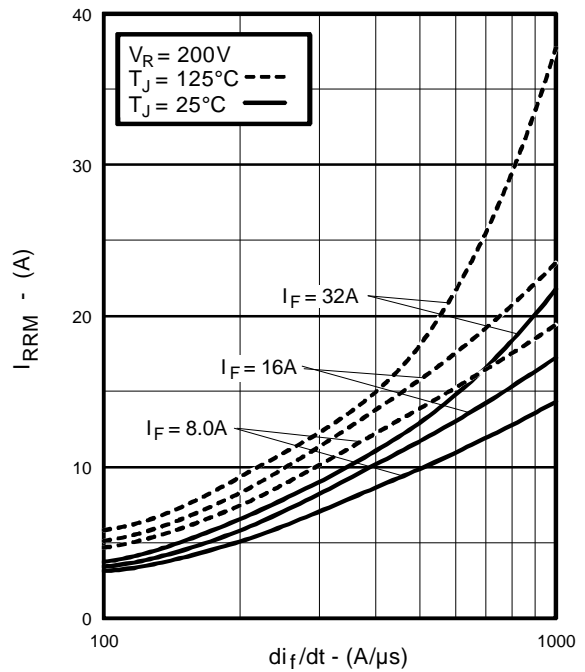


Fig. 15 - Typical Recovery Current vs. di_f/dt

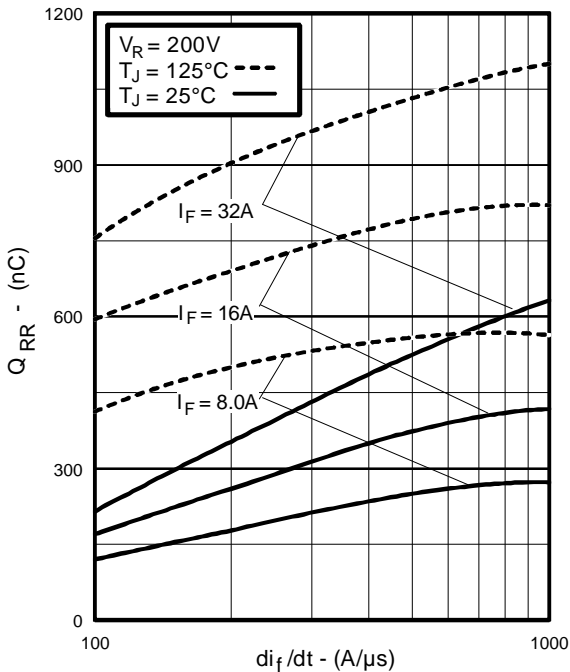


Fig. 16 - Typical Stored Charge vs. di_f/dt

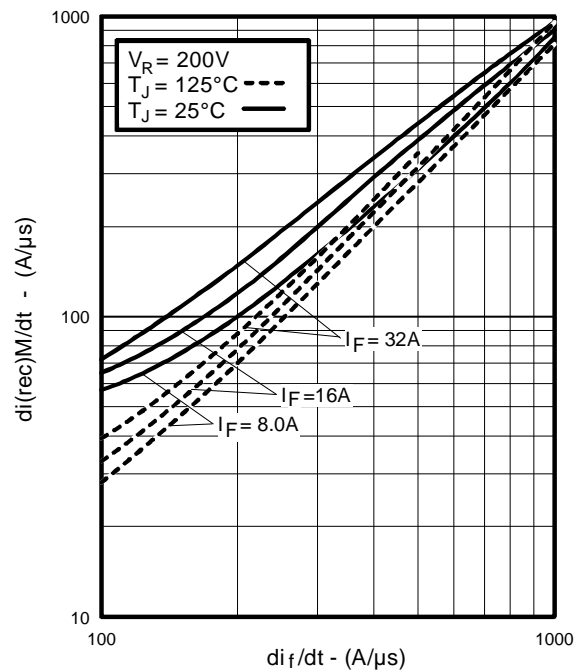


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

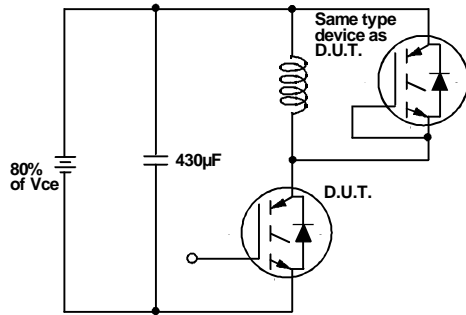


Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

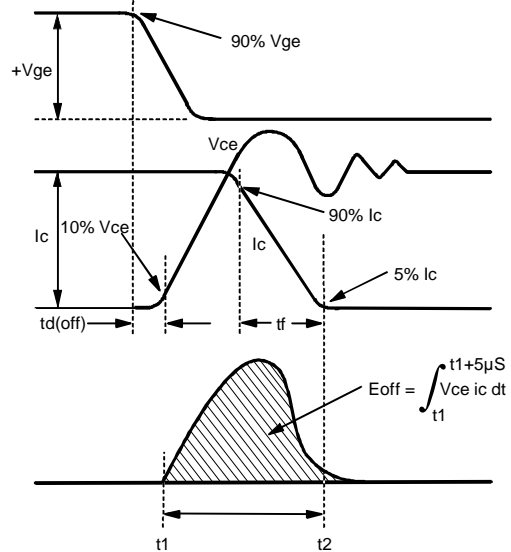


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

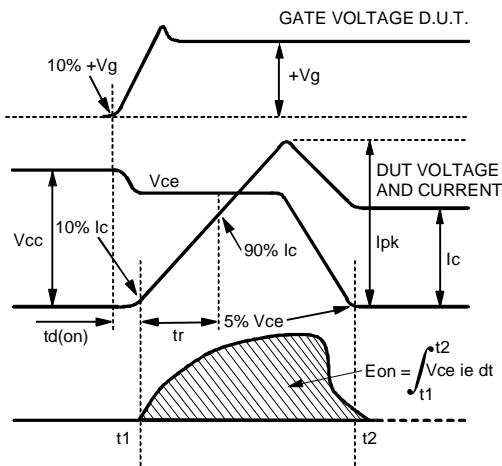


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

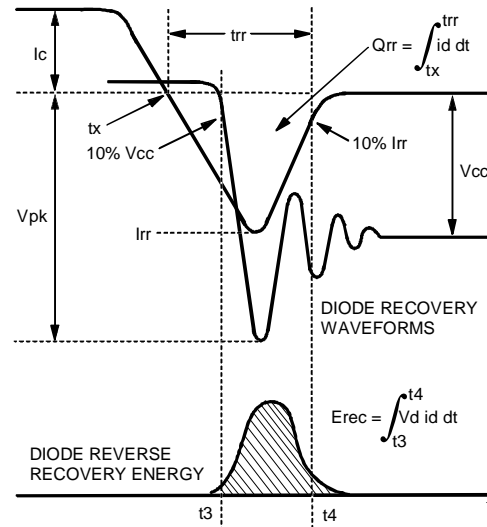


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

**Refer to Section D for the following:
Appendix H: Section D - page D-10**

Fig. 18e - Macro Waveforms for Test Circuit Fig. 18a

Fig. 19 - Clamped Inductive Load Test Circuit

Fig. 20 - Pulsed Collector Current Test Circuit